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2N7002PS 60 V, 320 mA N-channel Trench MOSFET Rev. 1 – 1 July 2010

Product data sheet

1. Product profile

1.1 General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
V _{DS}	drain-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-	60	V
V_{GS}	gate-source voltage	$T_{amb} = 25 \ ^{\circ}C$	-	-	±20	V
I _D	drain current	$T_{amb} = 25 \text{ °C};$ $V_{GS} = 10 \text{ V}$	<u>[1]</u> -	-	320	mA
R _{DSon}	drain-source on-state resistance	T _j = 25 °C; V _{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².



60 V, 320 mA N-channel Trench MOSFET

2. Pinning information

Table 2.	Pinning			
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1		
2	G1	gate1		D ₁ D ₂
3	D2	drain2		
4	S2	source2		(本武本武)
5	G2	gate2	1 2 3	
6	D1	drain1		$S_1 G_1 S_2 G_2$
				msd901

3. Ordering information

Table 3. Ordering information				
Type number	Package			
	Name	Description	Version	
2N7002PS	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 4. Marking codes	
Type number	Marking code ^[1]
2N7002PS	M8*
 * = -: made in Hong Kong * = p: made in Hong Kong * = t: made in Malaycia 	

- * = t: made in Malaysia
- * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
Per trans	istor				
V _{DS}	drain-source voltage	T _{amb} = 25 °C	-	60	V
V_{GS}	gate-source voltage	T _{amb} = 25 °C	-	±20	V
I _D drain current	drain current	V _{GS} = 10 V	<u>[1]</u>		
		$T_{amb} = 25 \ ^{\circ}C$	-	320	mA
		$T_{amb} = 100 \ ^{\circ}C$	-	240	mA
I _{DM}	peak drain current	$\begin{array}{l} T_{amb} = 25 \ ^{\circ}C; \\ single \ pulse; \ t_p \leq 10 \ \mu s \end{array}$	-	1.2	A

Product data sheet

60 V, 320 mA N-channel Trench MOSFET

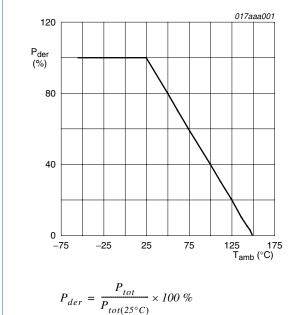
Table 5.	Limiting	values	continued
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In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation		[2] -	280	mW
			<u>[1]</u> -	320	mW
		T _{sp} = 25 °C	-	990	mW
Source-d	rain diode				
ls	source current	$T_{amb} = 25 \ ^{\circ}C$	<u>[1]</u> -	320	mA
Per devic	e				
P _{tot}	total power dissipation	$T_{amb} = 25 \ ^{\circ}C$	[2] _	420	mW
Tj	junction temperature			150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

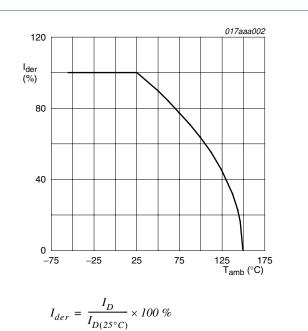
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.





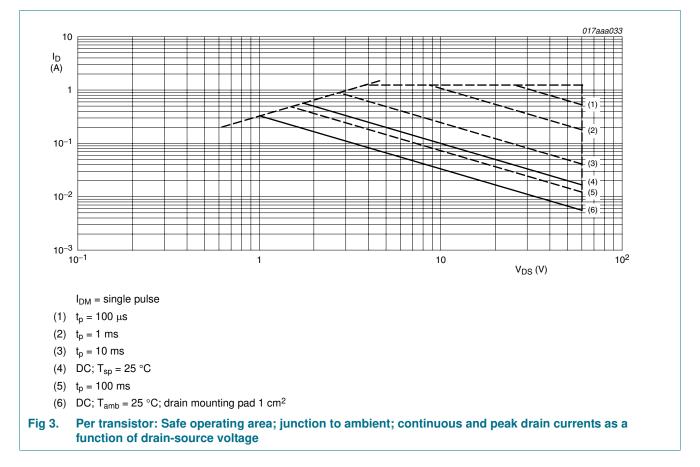






2N7002PS

60 V, 320 mA N-channel Trench MOSFET



6. Thermal characteristics

Symbol Parameter Conditions Per transistor Rth(j-a) thermal resistance from in free air iunction to ambient

R _{th(j-a)}	thermal resistance from	in free air	<u>[1]</u> -	390	445	K/W
	junction to ambient		[2] _	340	390	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	130	K/W
Per device						
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	300	K/W

Min

Тур

Мах

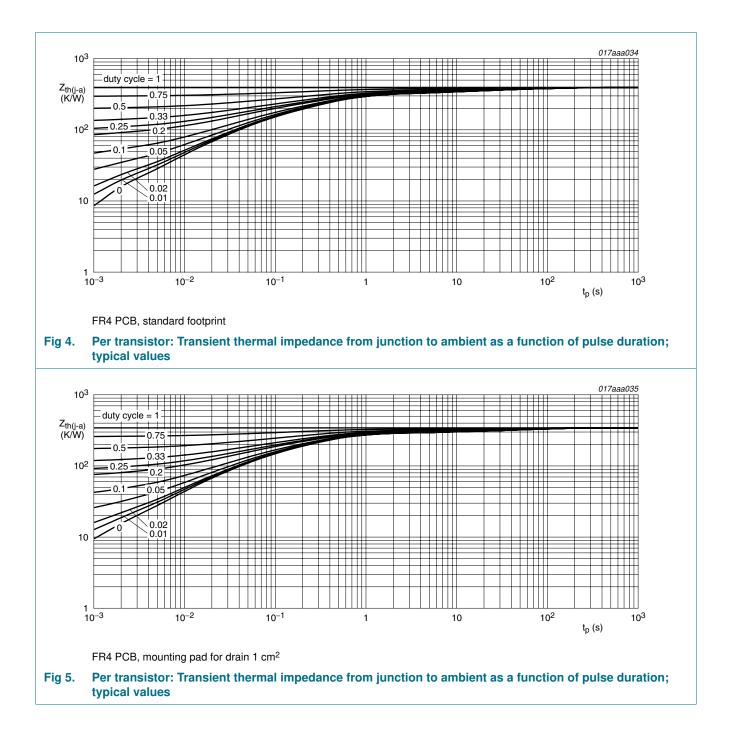
Unit

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

2N7002PS

60 V, 320 mA N-channel Trench MOSFET



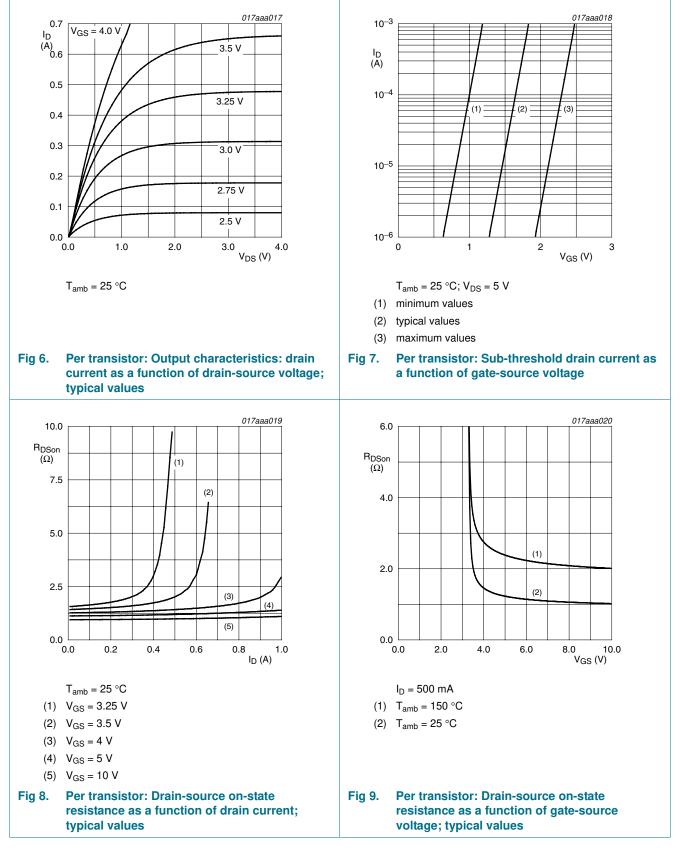
60 V, 320 mA N-channel Trench MOSFET

7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transi	stor					
Static char	acteristics					
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 10 \ \mu\text{A}; \ V_{GS} = 0 \ V$	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 250 \ \mu\text{A}; \ V_{DS} = V_{GS}$	1.1	1.75	2.4	V
I _{DSS}	drain leakage current	$V_{DS} = 60 \text{ V}; V_{GS} = 0 \text{ V}$				
		T _j = 25 °C	-	-	1	μA
		T _j = 150 °C	-	-	10	μA
I _{GSS}	gate leakage current	$V_{GS}=\pm 20~V;~V_{DS}=0~V$	-	-	100	nA
R _{DSon}	drain-source on-state		<u>[1]</u>			
	resistance	$V_{GS} = 5 \text{ V}; \text{ I}_{D} = 50 \text{ mA}$	-	1.3	2	Ω
		V_{GS} = 10 V; I _D = 500 mA	-	1	1.6	Ω
9 _{fs}	forward transconductance	$V_{DS} = 10 \text{ V}; \text{ I}_{D} = 200 \text{ mA}$	<u>[1]</u> -	400	-	mS
Dynamic c	haracteristics					
Q _{G(tot)}	total gate charge	I _D = 300 mA;	-	0.6	0.8	nC
Q _{GS}	gate-source charge	[–] V _{DS} = 30 V; – V _{GS} = 4.5 V	-	0.2	-	nC
Q _{GD}	gate-drain charge	$-v_{GS} = 4.5 v$	-	0.2	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 10 V;$	-	30	50	pF
Coss	output capacitance	f = 1 MHz	-	7	-	pF
C _{rss}	reverse transfer capacitance		-	4	-	pF
t _{d(on)}	turn-on delay time	V _{DD} = 50 V;	-	3	6	ns
t _r	rise time	$R_{L} = 250 \Omega;$	-	4	-	ns
t _{d(off)}	turn-off delay time	– V _{GS} = 10 V; R _G = 6 Ω	-	10	20	ns
t _f	fall time		-	5	-	ns
Source-dra	ain diode					
V _{SD}	source-drain voltage	I _S = 115 mA; V _{GS} = 0 V	0.47	0.75	1.1	V

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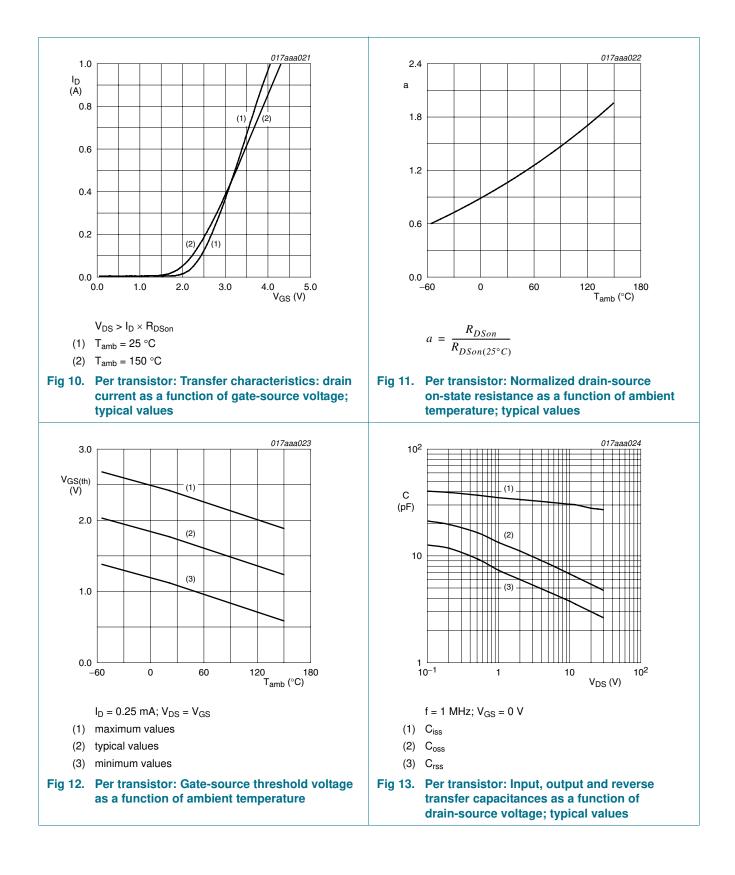
60 V, 320 mA N-channel Trench MOSFET



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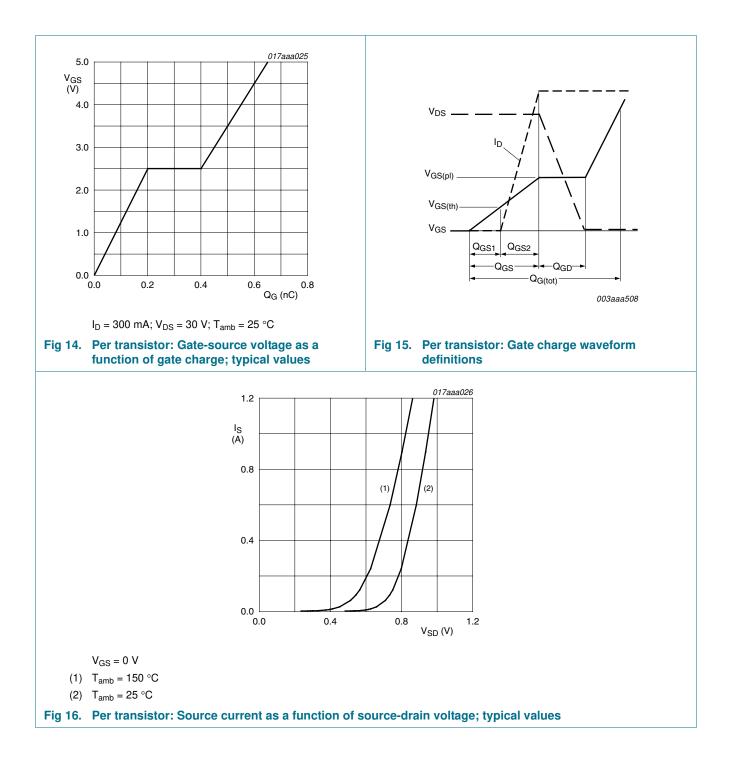
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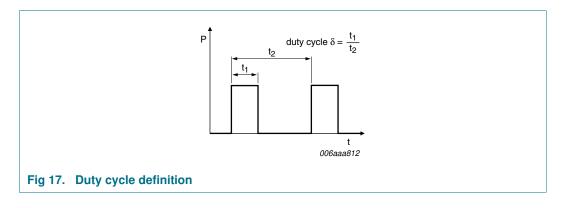
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60 V, 320 mA N-channel Trench MOSFET



60 V, 320 mA N-channel Trench MOSFET

8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

60 V, 320 mA N-channel Trench MOSFET

9. Package outline

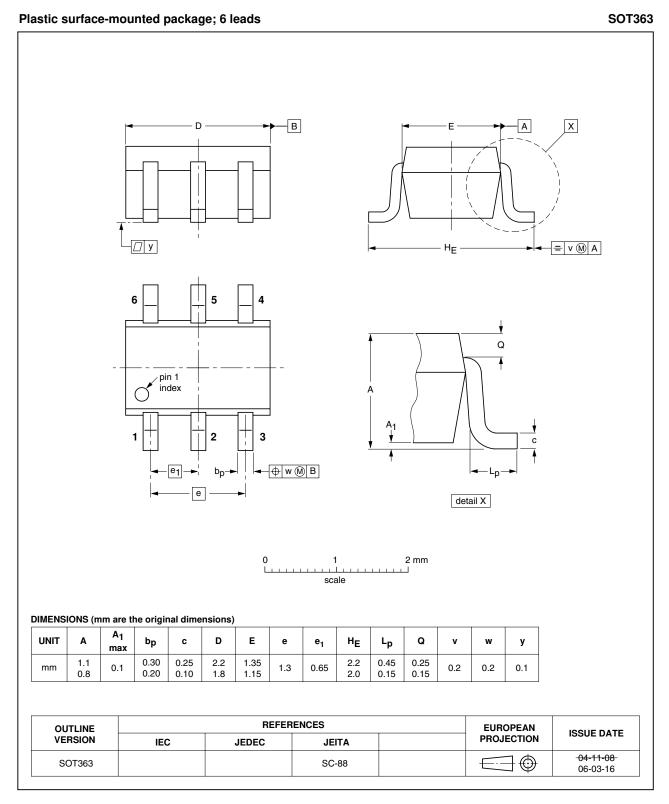
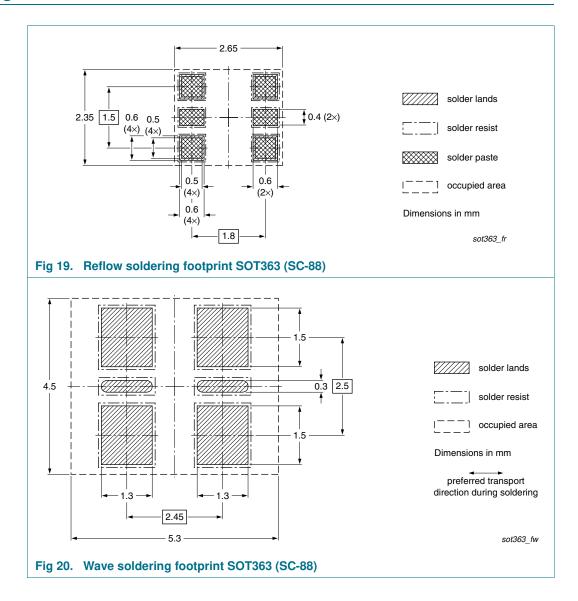


Fig 18. Package outline SOT363 (SC-88)

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60 V, 320 mA N-channel Trench MOSFET

10. Soldering



Product data sheet

60 V, 320 mA N-channel Trench MOSFET

11. Revision history

Table 8. R	Revision history				
Document ID		Release date	Data sheet status	Change notice	Supersedes
2N7002PS v.	1	20100701	Product data sheet	-	-

60 V, 320 mA N-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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60 V, 320 mA N-channel Trench MOSFET

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60 V, 320 mA N-channel Trench MOSFET

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